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December 2014

FCH041N60E

N-Channel SuperFET[®] II Easy-Drive MOSFET 600 V, 77 A, 41 m Ω

Features

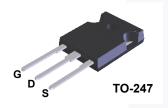
- 650 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 36 m Ω
- Ultra Low Gate Charge (Typ. Q_q = 285 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 735 pF)
- 100% Avalanche Tested
- · An Integrated Gate Resistor
- · RoHS Compliant

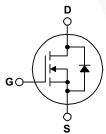
Applications

- · LCD / LED / PDP TV Lighting
- · Solar Inverter
- · AC-DC Power Supply

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET easy-drive series offers slightly slower rise and fall times compared to the SuperFET II MOSFET series. Noted by the "E" part number suffix, this family helps manage EMI issues and allows for easier design implementation. For faster switching in applications where switching losses must be at an absolute minimum, please consider the SuperFET II MOSFET series.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FCH041N60E	Unit
V _{DSS}	Drain to Source Voltage			600	V
V	Cata to Course Voltage	- DC		±20	V
V_{GSS}	/ _{GSS} Gate to Source Voltage	- AC	(f > 1 Hz)	±30	V
	Drain Current - Continuous (T _C = 25°C)			77	Α
ID	Drain Current	- Continuous (T _C = 100°C)		48.7	A
I _{DM}	Drain Current	- Pulsed (Note 1)		231	Α
E _{AS}	Single Pulsed Avalanche En	ergy	(Note 2)	2025	mJ
I _{AR}	Avalanche Current		(Note 1)	15	Α
E _{AR}	Repetitive Avalanche Energy	Repetitive Avalanche Energy (Note 1)		5.92	mJ
dv/dt	MOSFET dv/dt			100	V/ns
uv/ut	Peak Diode Recovery dv/dt		(Note 3)	20	V/IIS
n	Dawer Dissinction	(T _C = 25°C)		592	W
P_{D}	Power Dissipation	- Derate Above 25°C		4.74	W/°C
T _J , T _{STG}	Operating and Storage Temp	perature Range		-55 to +150	οС
T _L	Maximum Lead Temperature 1/8" from Case for 5 Second	3 .		300	°C

Thermal Characteristics

Symbol	Parameter	FCH041N60E	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.21	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	C/VV

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCH041N60E	FCH041N60E	TO-247	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	lest Conditions	win.	ıyp.	wax.	Unit
Off Chara	acteristics					
D\/	Drain to Source Breakdown Voltage	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}, T_C = 25^{\circ}\text{C}$	600	-	-	V
BV _{DSS} Drain to S	Diani to Source Breakdown voltage	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}, T_C = 150^{\circ}\text{C}$	650	-	-	v
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I _D = 10 mA, Referenced to 25°C	-	0.67	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μА
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	9.7	-	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$		-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.5	-	3.5	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 39 \text{ A}$	-	36	41	$m\Omega$
9 _{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_{D} = 39 \text{ A}$	-	71	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 400 V V 0 V	-	10300	13700	pF
C _{oss}	Output Capacitance	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	- \	355	475	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12	-	4	6	pF
Coss	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz	-	187	-	pF
C _{oss} eff.	Effective Output Capacitance	V _{DS} = 0 V to 480 V, V _{GS} = 0 V	-	735	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 380 V, I _D = 39 A,	-	285	380	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	45	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	105	-	nC
ESR	Equivalent Series Resistance	f = 1 MHz	-	1.2	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		- /	50	110	ns
t _r	Turn-On Rise Time	$V_{DD} = 380 \text{ V}, I_D = 39 \text{ A},$	-/	50	110	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 4.7 Ω	-	320	650	ns
t _f	Turn-Off Fall Time	(Note 4)	-	85	180	ns

Drain-Source Diode Characteristics

Maximum Continuous Drain to Source Diode Forward Current			-	77	Α
Maximum Pulsed Drain to Source Diode Forward Current		-	-	231	Α
Drain to Source Diode Forward Voltage V _{GS} = 0 V, I _{SD} = 39 A		-	-	1.2	V
Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 39 A,	-	590	-/-	ns
Reverse Recovery Charge $dI_F/dt = 100 \text{ A}/\mu\text{s}$		-	18	-	μС
	Drain to Source Diode Forward Voltage Reverse Recovery Time	Drain to Source Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_{SD} = 39 \text{ A}$ Reverse Recovery Time $V_{GS} = 0 \text{ V}, I_{SD} = 39 \text{ A},$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Drain to Source Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_{SD} = 39 \text{ A}$ Severse Recovery Time $V_{GS} = 0 \text{ V}, I_{SD} = 39 \text{ A},$ - 590	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

Notes:

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} I_{AS} = 15 A, R_{G} = 25 Ω , starting T_{J} = 25°C.

^{3.} $I_{SD} \le 39$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le 380$ V, starting T_J = 25°C.

^{4.} Essentially independent of operating temperature.

Typical Characteristics

Figure 1. On-Region Characteristics

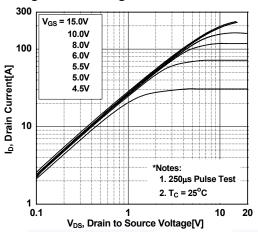


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

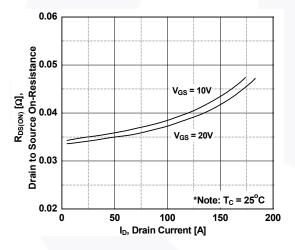


Figure 5. Capacitance Characteristics

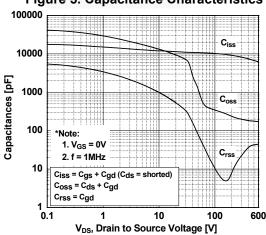


Figure 2. Transfer Characteristics

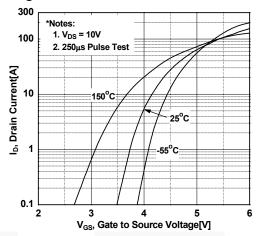


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

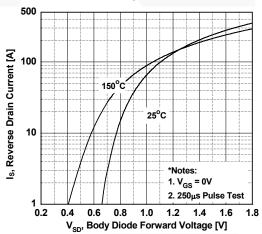
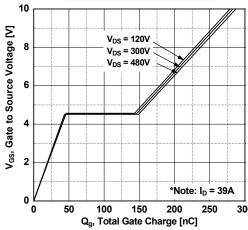


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

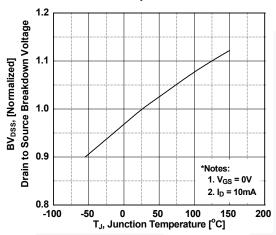


Figure 9. Maximum Safe Operating Area

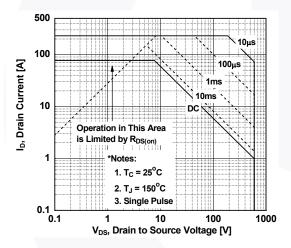


Figure 11. Eoss vs. Drain to Source Voltage

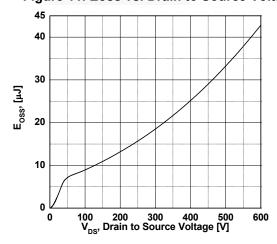


Figure 8. On-Resistance Variation vs. Temperature

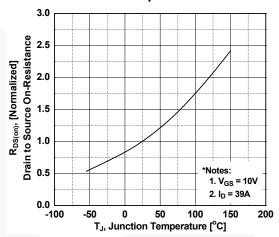
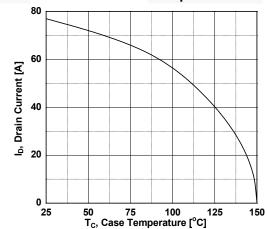
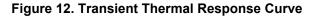
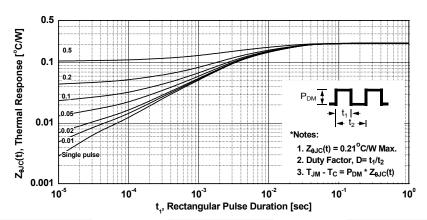


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Characteristics (Continued)





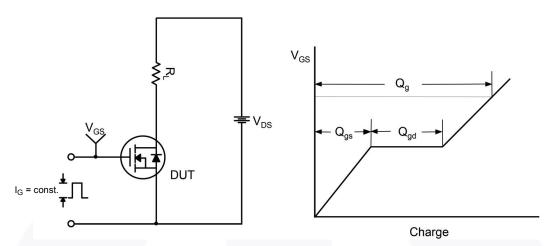


Figure 13. Gate Charge Test Circuit & Waveform

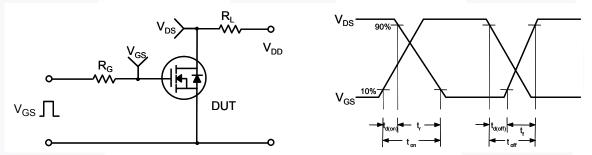


Figure 14. Resistive Switching Test Circuit & Waveforms

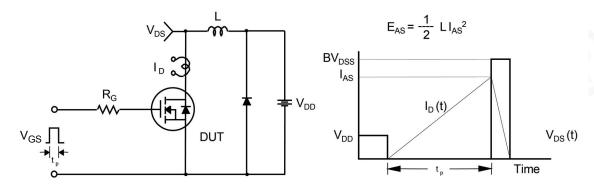


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

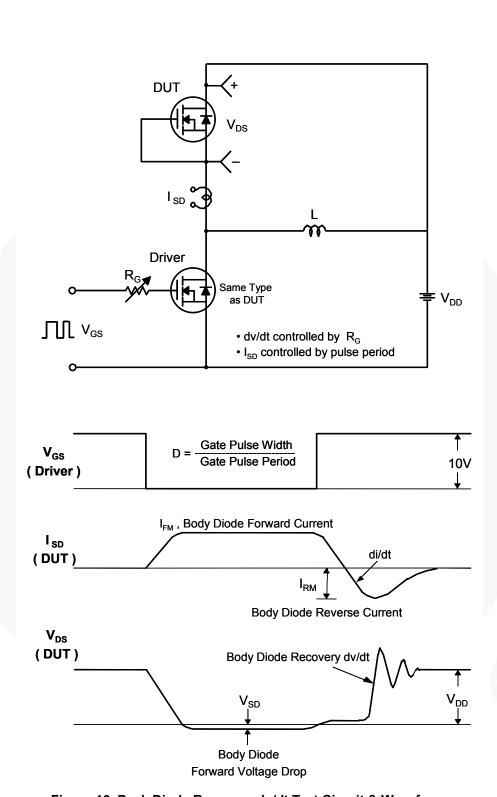
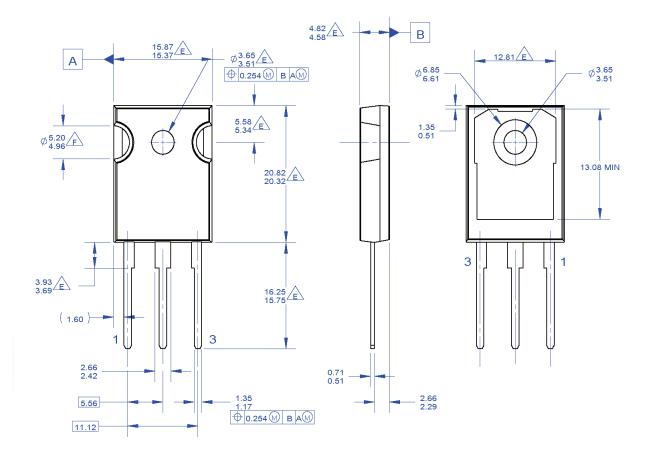


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

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- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS
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- D. DRAWING CONFORMS TO ASME Y14.5 1994

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F NOTCH MAY BE SQUARE

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Figure 17. TO-247, Molded, 3-Lead, Jedec Variation AB

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Definition of Terms

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